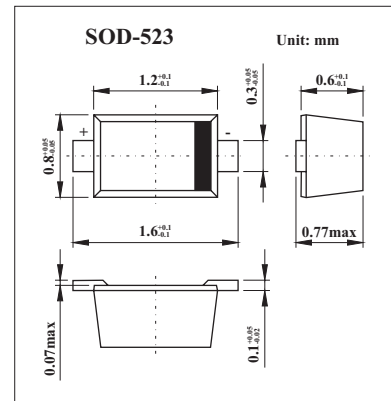


## Silicon Schottky Barrier Diode

## HSC276

## ■ Features

- High forward current, Low capacitance.
- Ultra small Flat Package (UFP) is suitable for surface mount design.



## ■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	3	V
Average rectified current	I <sub>o</sub>	30	mA
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

## ■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	V <sub>R</sub>	I <sub>R</sub> = 10 μA	30			V
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 0.5 V			0.5	μA
Forward voltage	V <sub>F</sub>	V <sub>R</sub> = 0.5 V	35			mV
Capacitance	C	V <sub>R</sub> = 0.5 V, f = 1 MHz			0.85	pF
ESD-Capability (Note 1)		C=200pF, Both forward and reverse direction 1 pulse.	30			V

## Note

1. Failure criterion ; I<sub>R</sub> ≥ 100mA at V<sub>R</sub> = 0.5 V

## ■ Marking

Marking	C2
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